

STPS12045TV

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	2 x 60 A		
V _{RRM}	45 V		
V _F (max)	0.67 V		

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- EXTREMELY FAST SWTICHING
- INSULATED PACKAGE: Insulating voltage = 2500 V(RMS)

DESCRIPTION

Dual power Schottky rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters.

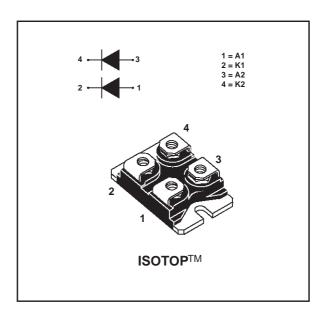
Packaged in ISOTOP, this device is especially intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	RMS forward current	Per diode	125	А	
I _{F(AV)}	Average forward current	$Tc = 100^{\circ}C$ $\delta = 0.5$	Per diode Per device	60 120	A
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	Per diode	700	А
I _{RRM}	Repetitive peak reverse current	tp = 2 μs F = 1kHz	Per diode	2	А
T _{stg}	Storage temperature range			- 65 to + 150	°C
Tj	Maximum junction temperature			100	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/µs

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit	
Rth (j-c)	Junction to case	Per diode	1	°C/W
		Total	0.55	
Rth (c)	Coupling	Coupling	0.1	

When the diodes 1 and 2 are used simultaneously :

 Δ Tj(diode 1) = P(diode) x R_{th}(Per diode) + P(diode 2) x R_{th(c)}

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Тур.	Max.	Unit
I _R *	Reverse leakage current	Tj = 25°C	V _R = V _{RRM}			1	mA
		Tj = 125°C				150	
V _F *	Forward voltage drop	Tj = 125°C	$I_F = 60 A$			0.67	V
		Tj = 25°C	I _F = 120 A			0.91	
		Tj = 125°C	I _F = 120 A			0.87	

Pulse test : * tp = 5 ms, δ < 2% ** tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation : P = 0.47 x $I_{F(AV)}$ + 0.00333 x ${I_F}^2_{(RMS)}$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

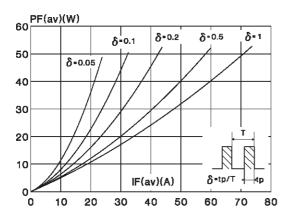
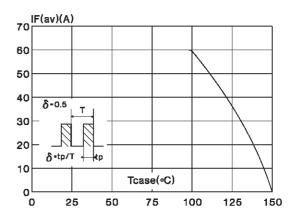


Fig. 2: Average current versus case temperature (δ = 0.5) (per diode).



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Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

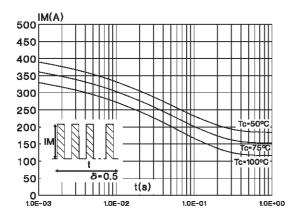


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

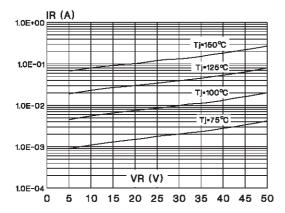


Fig. 7: Forward voltage drop versus forward current (maximum values) (per diode).

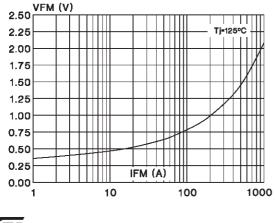


Fig.4 : Relative variation of thermal transient impedance junction to case versus pulse duration.

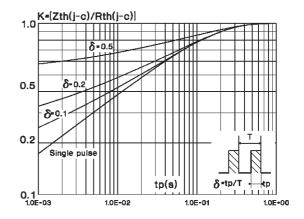
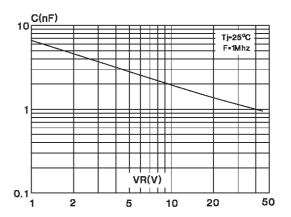


Fig. 6: Junction capacitance versus reverse voltage applied (typical values) (per diode).

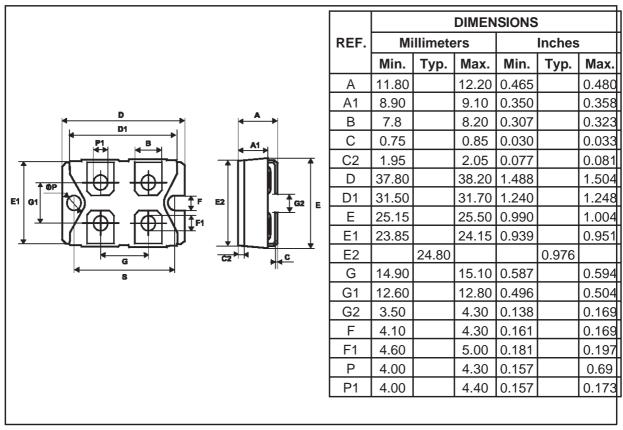




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PACKAGE MECHANICAL DATA

ISOTOP



- Marking: STPS12045TV
- Cooling method: C
- Weight: 28 g.

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